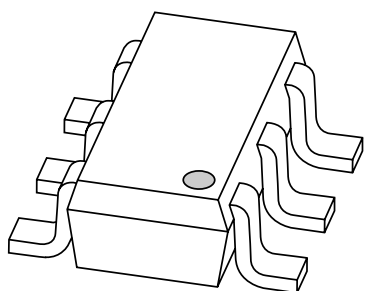


DATA SHEET



PMEM4010PD

PNP transistor/Schottky diode
module

Product specification

2002 Oct 28

PNP transistor/Schottky diode module

PMEM4010PD

FEATURES

- 600 mW total power dissipation
- High current capability
- Reduces required PCB area
- Reduced pick and place costs
- Small plastic SMD package.

Transistor:

- Low collector-emitter saturation voltage.

Diode:

- Ultra high-speed switching
- Very low forward voltage
- Guard ring protected.

APPLICATIONS

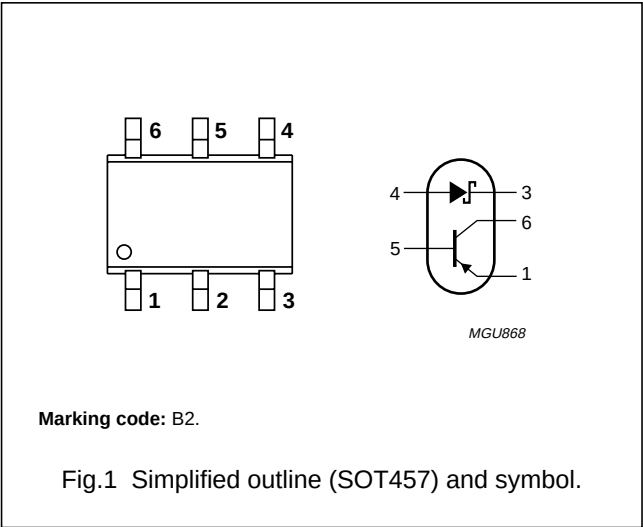
- DC/DC convertors
- Inductive load drivers
- General purpose load drivers
- Reverse polarity protection circuits.

DESCRIPTION

Combination of a PNP transistor with low V_{CEsat} and high current capability and a planar Schottky barrier diode with an integrated guard ring for stress protection in a SOT457 (SC-74) small plastic package.
NPN complement: PMEM4010ND.

PINNING

PIN	DESCRIPTION
1	emitter
2	not connected
3	cathode
4	anode
5	base
6	collector



PNP transistor/Schottky diode module

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
NPN transistor					
V_{CBO}	collector-base voltage	open emitter	–	–40	V
V_{CEO}	collector-emitter voltage	open base	–	–40	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–1	A
I_{CM}	peak collector current		–	–2	A
I_{BM}	peak base current		–	–1	A
T_j	junction temperature		–	150	°C
Schottky barrier diode					
V_R	continuous reverse voltage		–	20	V
I_F	continuous forward current		–	1	A
I_{FSM}	non repetitive peak forward current	$t = 8.3$ ms half sinewave; JEDEC method	–	5	A
T_j	junction temperature		–	125	°C
Combined device					
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C; note 1	–	600	mW
T_{stg}	storage temperature		–65	+150	°C
T_{amb}	operating ambient temperature		–65	+125	°C

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air; note 1	208	K/W

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².

PNP transistor/Schottky diode module

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CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

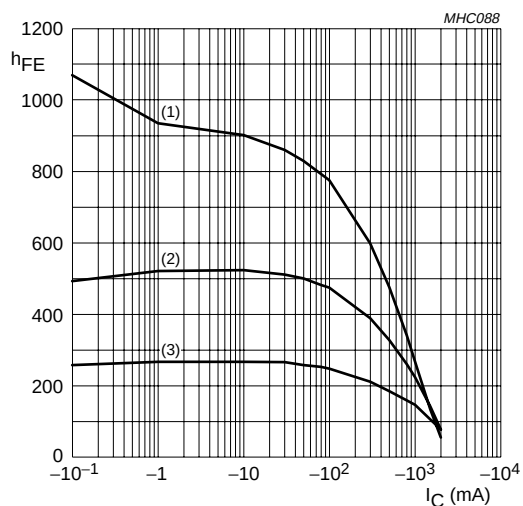
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
NPN transistor						
I_{CBO}	collector-base cut-off current	$V_{CB} = -40\text{ V}; I_E = 0$	–	–	–100	nA
		$V_{CB} = -40\text{ V}; I_E = 0;$ $T_{amb} = 150\text{ }^{\circ}\text{C}$	–	–	–50	μA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = -30\text{ V}; I_B = 0$	–	–	–100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0$	–	–	–100	nA
h_{FE}	DC current gain	$V_{CE} = -5\text{ V}; I_C = -1\text{ mA}$	300	–	–	
		$V_{CE} = -5\text{ V}; I_C = -100\text{ mA}$	300	–	800	
		$V_{CE} = -5\text{ V}; I_C = -500\text{ mA}$	250	–	–	
		$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	160	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -100\text{ mA}; I_B = -1\text{ mA}$	–	–	–140	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	–	–	–170	mV
		$I_C = -1\text{ A}; I_B = -100\text{ mA}$	–	–	–310	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -1\text{ A}; I_B = -50\text{ mA}$	–	–	–1.1	V
R_{CEsat}	equivalent on-resistance	$I_C = -500\text{ mA}; I_B = -50\text{ mA};$ note 1	–	300	<340	$\text{m}\Omega$
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	–	–	–1	V
f_T	transition frequency	$I_C = -50\text{ mA}; V_{CE} = -10\text{ V};$ $f = 100\text{ MHz}$	150	–	–	MHz
Schottky barrier diode						
V_F	continuous forward voltage	$I_F = 10\text{ mA};$ note 1	–	240	270	mV
		$I_F = 100\text{ mA};$ note 1	–	300	350	mV
		$I_F = 1000\text{ mA};$ see Fig.7; note 1	–	480	550	mV
I_R	reverse current	$V_R = 5\text{ V};$ note 1	–	5	10	μA
		$V_R = 8\text{ V};$ note 1	–	7	20	μA
		$V_R = 15\text{ V};$ see Fig.8; note 1	–	10	50	μA
C_d	diode capacitance	$V_R = 5\text{ V}; f = 1\text{ MHz};$ see Fig.9	–	19	25	pF

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.

PNP transistor/Schottky diode module

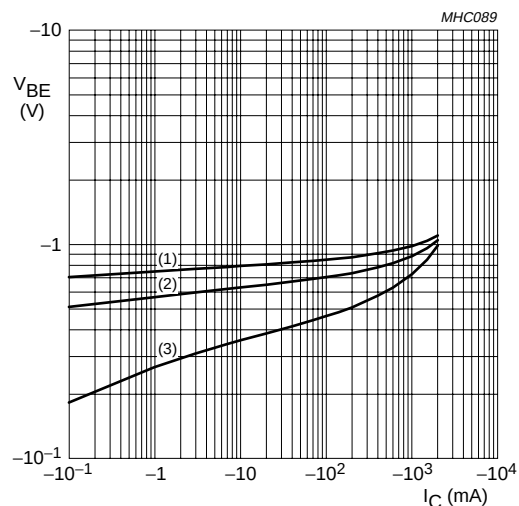
PMEM4010PD



PNP transistor; $V_{CE} = -5$ V.

- (1) $T_{amb} = 150$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = -55$ °C.

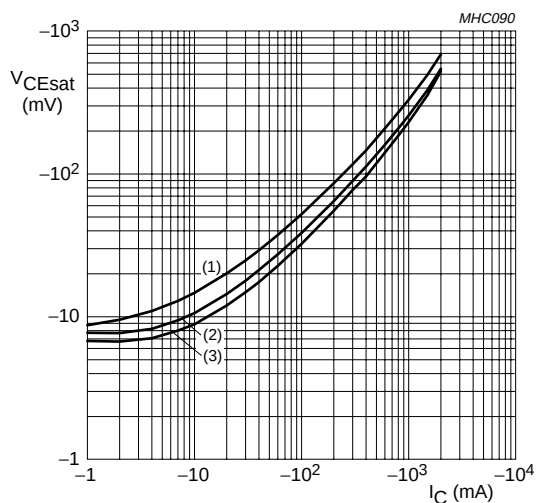
Fig.2 DC current gain as a function of collector current; typical values.



PNP transistor; $V_{CE} = -5$ V.

- (1) $T_{amb} = -55$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = 150$ °C.

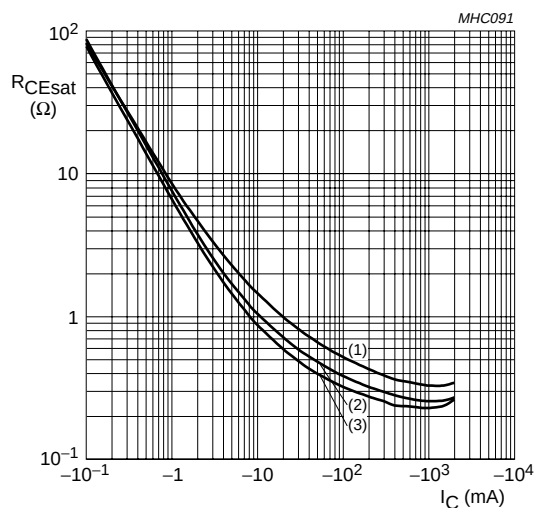
Fig.3 Base-emitter voltage as a function of collector current; typical values.



PNP transistor; $I_C/I_B = 10$.

- (1) $T_{amb} = 150$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = -55$ °C.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



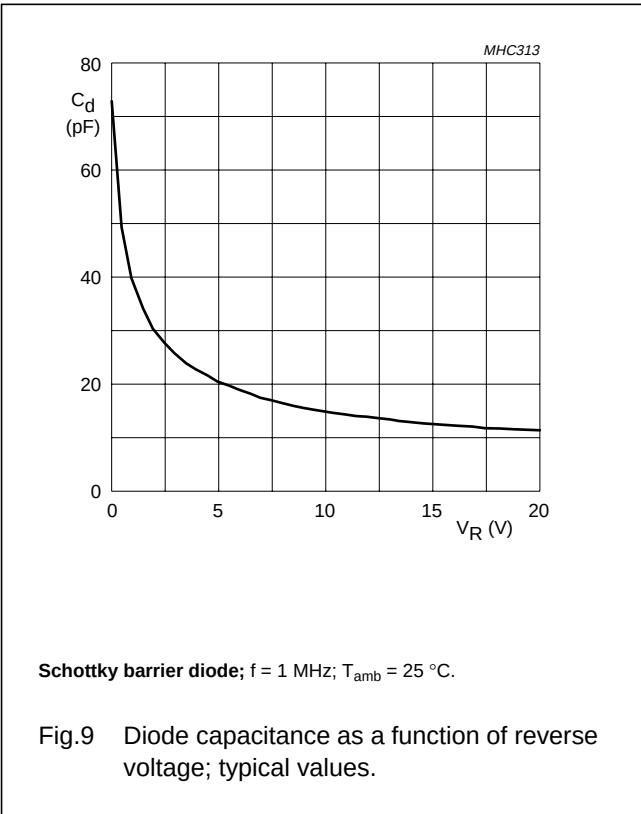
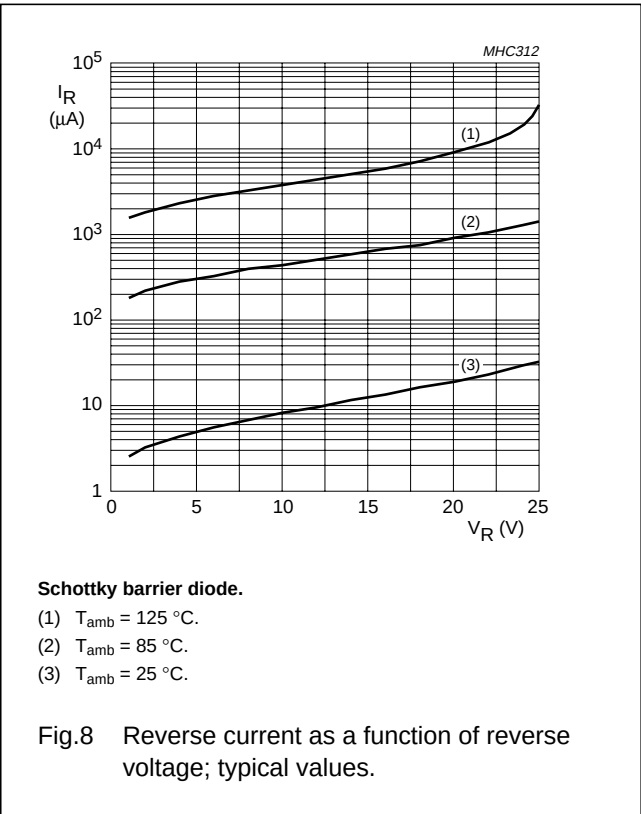
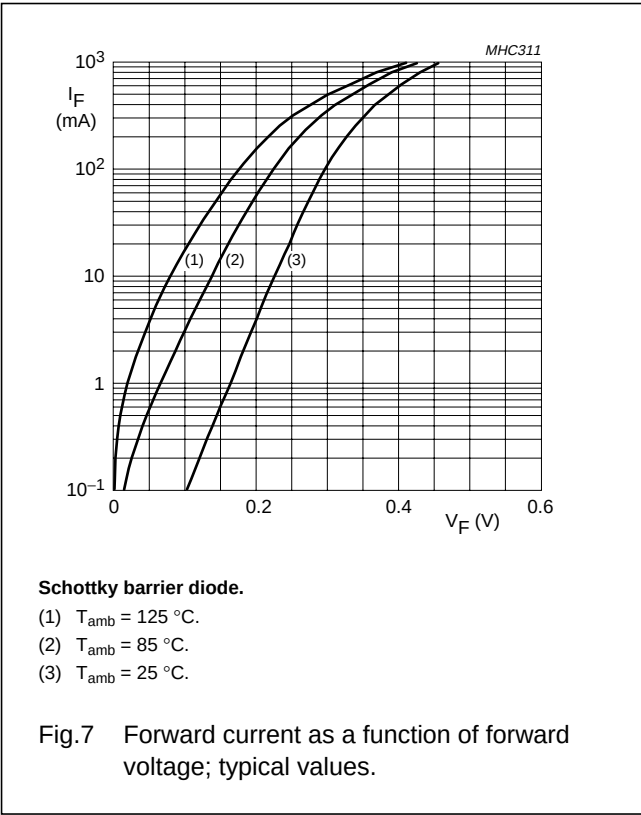
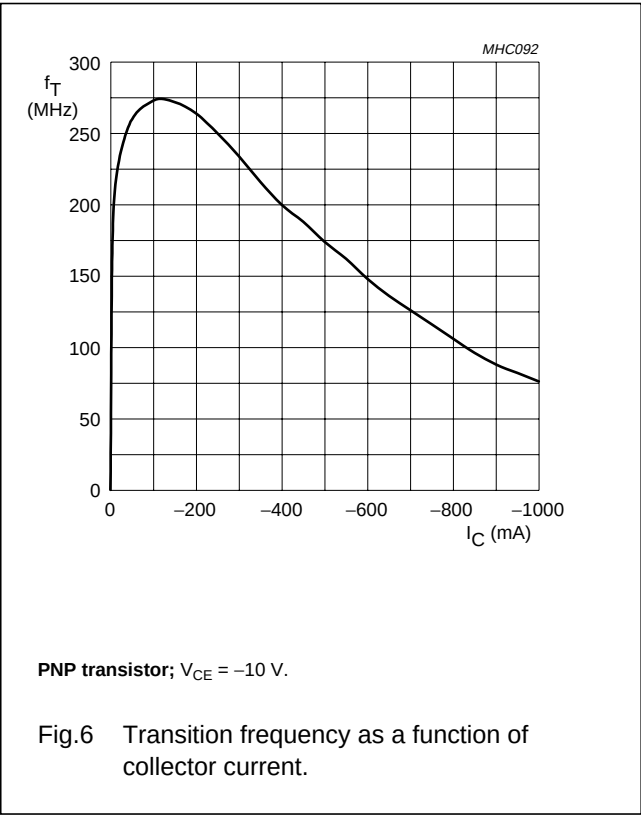
PNP transistor; $I_C/I_B = 10$.

- (1) $T_{amb} = 150$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = -55$ °C.

Fig.5 Equivalent on-resistance as a function of collector current; typical values.

PNP transistor/Schottky diode module

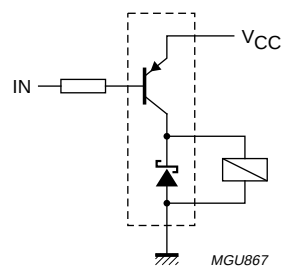
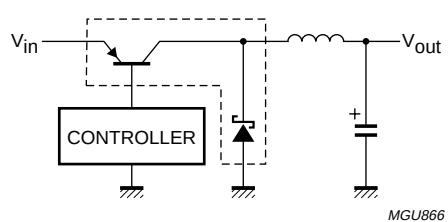
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PNP transistor/Schottky diode module

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APPLICATION INFORMATION



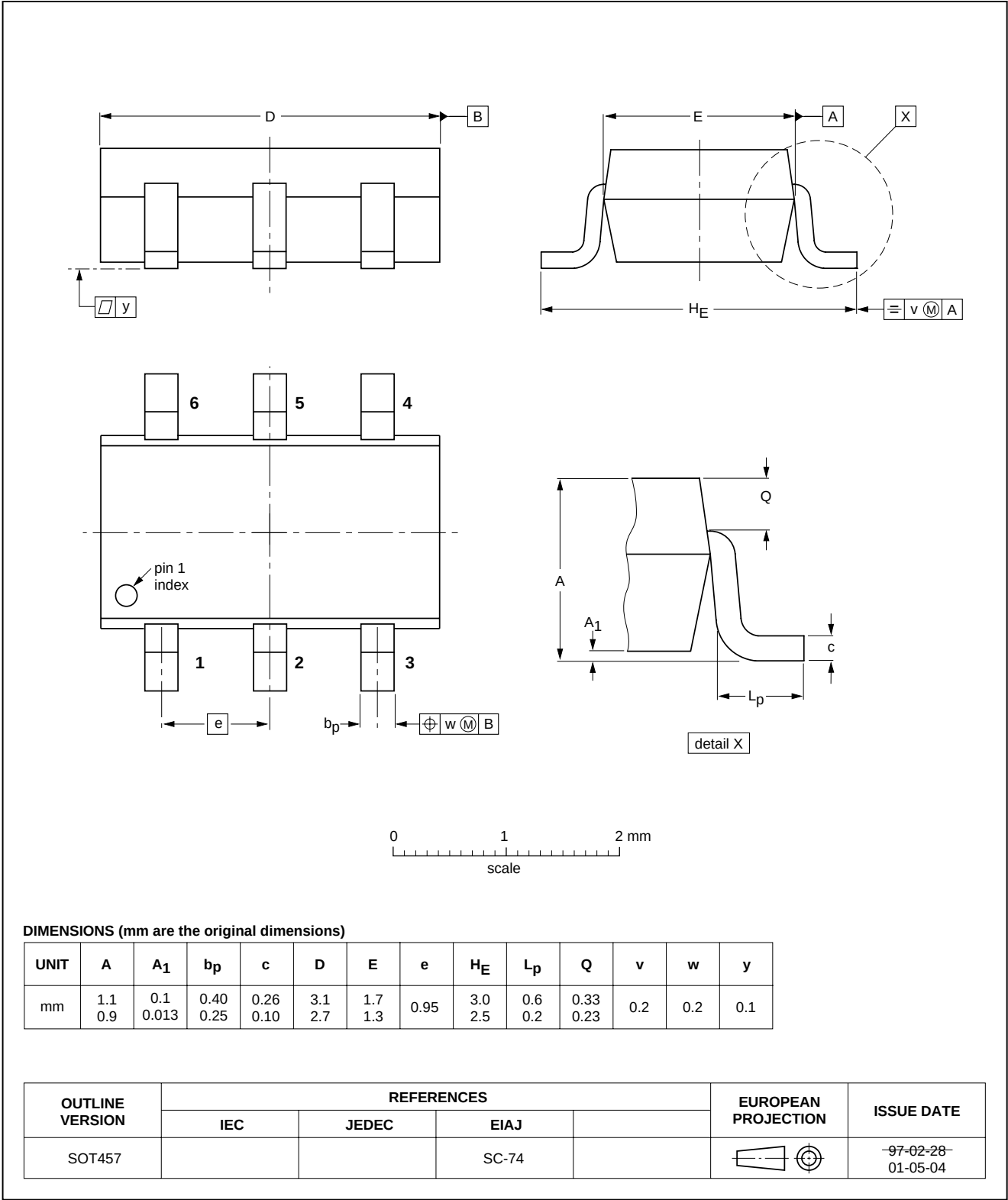
PNP transistor/Schottky diode module

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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT457



PNP transistor/Schottky diode module

PMEM4010PD

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
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NOTES

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NOTES

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Contact information

For additional information please visit <http://www.semiconductors.philips.com>. Fax: **+31 40 27 24825**

For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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